

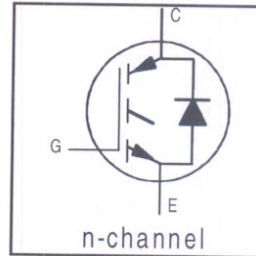
IRG4BC20SDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH
 ULTRAFAST SOFT RECOVERY DIODE

Standard Speed IGBT

Features

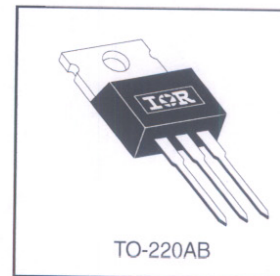
- Extremely low voltage drop 1.4Vtyp. @ 10A
- S-Series: Minimizes power dissipation at up to 3 KHz PWM frequency in inverter drives, up to 4 KHz in brushless DC drives.
- Very Tight Vce(on) distribution
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard TO-220AB package
- Lead-Free



| |
|----------------------------------|
| $V_{CES} = 600V$ |
| $V_{CE(on)} \text{ typ.} = 1.4V$ |
| @ $V_{GE} = 15V, I_C = 10A$ |

Benefits

- Generation 4 IGBT's offer highest efficiencies available
- IGBT's optimized for specific application conditions
- HEXFRED diodes optimized for performance with IGBT's. Minimized recovery characteristics require less/no snubbing
- Lower losses than MOSFET's conduction and Diode losses



Absolute Maximum Ratings

| | Parameter | Max. | Units |
|---------------------------|------------------------------------|-----------------------------------|------------|
| V_{CES} | Collector-to-Emitter Voltage | 600 | V |
| $I_C @ T_C = 25^\circ C$ | Continuous Collector Current | 19 | A |
| $I_C @ T_C = 100^\circ C$ | Continuous Collector Current | 10 | |
| I_{CM} | Pulsed Collector Current ① | 38 | |
| I_{LM} | Clamped Inductive Load Current ② | 38 | |
| $I_F @ T_C = 100^\circ C$ | Diode Continuous Forward Current | 7.0 | |
| I_{FM} | Diode Maximum Forward Current | 38 | |
| V_{GE} | Gate-to-Emitter Voltage | ± 20 | V |
| $P_D @ T_C = 25^\circ C$ | Maximum Power Dissipation | 60 | W |
| $P_D @ T_C = 100^\circ C$ | Maximum Power Dissipation | 24 | |
| T_J | Operating Junction and | -55 to +150 | $^\circ C$ |
| T_{STG} | Storage Temperature Range | | |
| | Soldering Temperature, for 10 sec. | 300 (0.063 in. (1.6mm) from case) | |
| | Mounting Torque, 6-32 or M3 Screw. | 10 lbf•in (1.1 N•m) | |

Thermal Resistance

| | Parameter | Min. | Typ. | Max. | Units |
|-----------------|---|------|----------|------|--------------|
| $R_{\theta JC}$ | Junction-to-Case - IGBT | — | — | 2.1 | $^\circ C/W$ |
| $R_{\theta JC}$ | Junction-to-Case - Diode | — | — | 3.5 | |
| $R_{\theta CS}$ | Case-to-Sink, flat, greased surface | — | 0.50 | — | |
| $R_{\theta JA}$ | Junction-to-Ambient, typical socket mount | — | — | 80 | |
| Wt | Weight | — | 2 (0.07) | — | g (oz) |

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---------------------------------|---|------|------|-----------|---------|---|
| $V_{(BR)CES}$ | Collector-to-Emitter Breakdown Voltage _f | 600 | — | — | V | $V_{GE} = 0V, I_C = 250\mu A$ |
| $\Delta V_{(BR)CES}/\Delta T_J$ | Temperature Coeff. of Breakdown Voltage | — | 0.75 | — | V/°C | $V_{GE} = 0V, I_C = 1.0mA$ |
| $V_{CE(on)}$ | Collector-to-Emitter Saturation Voltage | — | 1.40 | 1.6 | V | $I_C = 10A$ $V_{GE} = 15V$ $I_C = 19A$ See Fig. 2, 5 $I_C = 10A, T_J = 150^\circ\text{C}$ |
| | | — | 1.85 | — | | |
| | | — | 1.44 | — | | |
| $V_{GE(th)}$ | Gate Threshold Voltage | 3.0 | — | 6.0 | | $V_{CE} = V_{GE}, I_C = 250\mu A$ |
| $\Delta V_{GE(th)}/\Delta T_J$ | Temperature Coeff. of Threshold Voltage | — | -11 | — | mV/°C | $V_{CE} = V_{GE}, I_C = 250\mu A$ |
| g_{fe} | Forward Transconductance ④ | 2.0 | 5.8 | — | S | $V_{CE} = 100V, I_C = 10A$ |
| I_{CES} | Zero Gate Voltage Collector Current | — | — | 250 | μA | $V_{GE} = 0V, V_{CE} = 600V$ $V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$ |
| | | — | — | 1700 | | |
| V_{FM} | Diode Forward Voltage Drop | — | 1.4 | 1.7 | V | $I_C = 8.0A$ See Fig. 13 $I_C = 8.0A, T_J = 150^\circ\text{C}$ |
| | | — | 1.3 | 1.6 | | |
| I_{GES} | Gate-to-Emitter Leakage Current | — | — | ± 100 | nA | $V_{GE} = \pm 20V$ |

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|------------------|--|------|------|------|------------|--|
| Q_g | Total Gate Charge (turn-on) | — | 27 | 40 | nC | $I_C = 10A$ $V_{CC} = 400V$ See Fig. 8 $V_{GE} = 15V$ |
| Q_{ge} | Gate - Emitter Charge (turn-on) | — | 4.3 | 6.5 | | |
| Q_{gc} | Gate - Collector Charge (turn-on) | — | 10 | 15 | | |
| $t_{d(on)}$ | Turn-On Delay Time | — | 62 | — | ns | $T_J = 25^\circ\text{C}$ $I_C = 10A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$ Energy losses include "tail" and diode reverse recovery. See Fig. 9, 10, 11, 18 |
| t_r | Rise Time | — | 32 | — | | |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 690 | 1040 | | |
| t_f | Fall Time | — | 480 | 730 | | |
| E_{on} | Turn-On Switching Loss | — | 0.32 | — | mJ | See Fig. 9, 10, 11, 18 |
| E_{off} | Turn-Off Switching Loss | — | 2.58 | — | | |
| E_{ts} | Total Switching Loss | — | 2.90 | 4.5 | | |
| $t_{d(on)}$ | Turn-On Delay Time | — | 64 | — | ns | $T_J = 150^\circ\text{C}$, See Fig. 10, 11, 18 $I_C = 10A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$ Energy losses include "tail" and diode reverse recovery. |
| t_r | Rise Time | — | 35 | — | | |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 980 | — | | |
| t_f | Fall Time | — | 800 | — | | |
| E_{ts} | Total Switching Loss | — | 4.33 | — | mJ | |
| L_E | Internal Emitter Inductance | — | 7.5 | — | nH | Measured 5mm from package |
| C_{ies} | Input Capacitance | — | 550 | — | pF | $V_{GE} = 0V$ $V_{CC} = 30V$ See Fig. 7 $f = 1.0MHz$ |
| C_{oes} | Output Capacitance | — | 39 | — | | |
| C_{res} | Reverse Transfer Capacitance | — | 7.1 | — | | |
| t_{rr} | Diode Reverse Recovery Time | — | 37 | 55 | ns | $T_J = 25^\circ\text{C}$ See Fig. 14 $T_J = 125^\circ\text{C}$ 14 |
| | | — | 55 | 90 | | |
| I_{rr} | Diode Peak Reverse Recovery Current | — | 3.5 | 5.0 | A | $T_J = 25^\circ\text{C}$ See Fig. 15 $T_J = 125^\circ\text{C}$ 15 |
| | | — | 4.5 | 8.0 | | |
| Q_{rr} | Diode Reverse Recovery Charge | — | 65 | 138 | nC | $T_J = 25^\circ\text{C}$ See Fig. 16 $T_J = 125^\circ\text{C}$ 16 |
| | | — | 124 | 360 | | |
| $di_{(rec)M}/dt$ | Diode Peak Rate of Fall of Recovery During t_b | — | 240 | — | A/ μs | $T_J = 25^\circ\text{C}$ See Fig. 17 $T_J = 125^\circ\text{C}$ 17 |
| | | — | 210 | — | | |

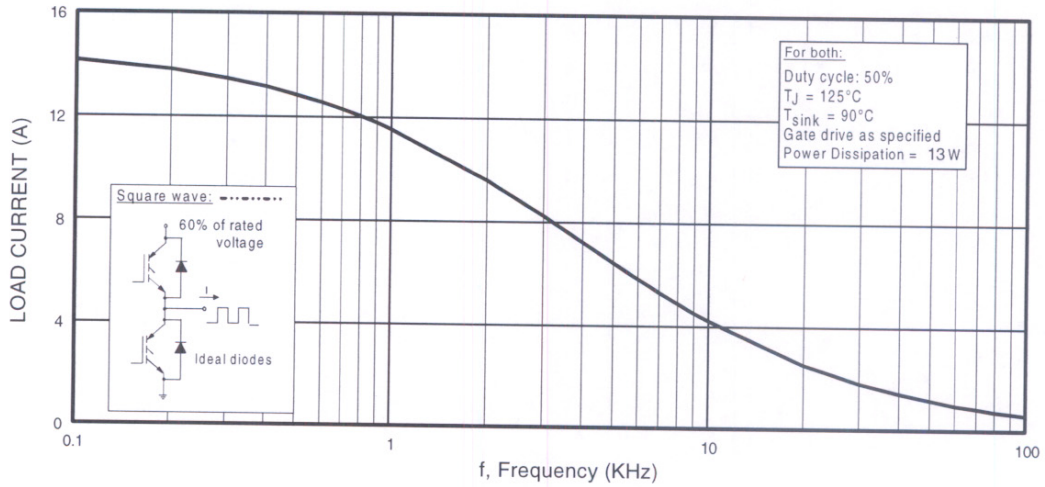


Fig. 1 - Typical Load Current vs. Frequency
 (Load Current = I_{RMS} of fundamental)

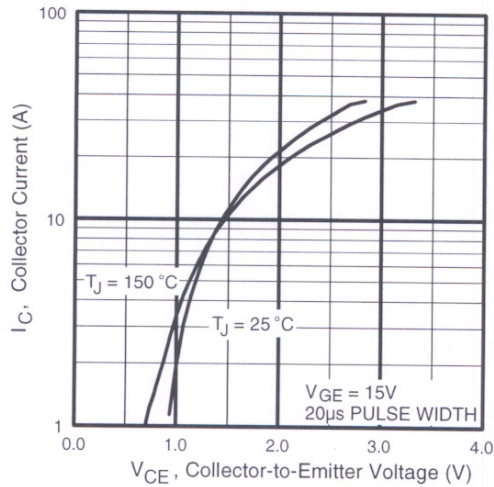


Fig. 2 - Typical Output Characteristics

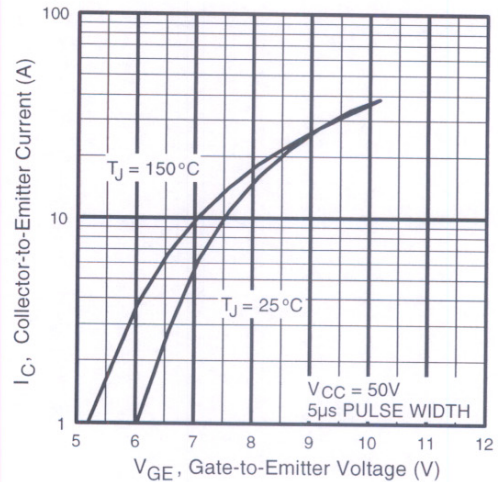


Fig. 3 - Typical Transfer Characteristics

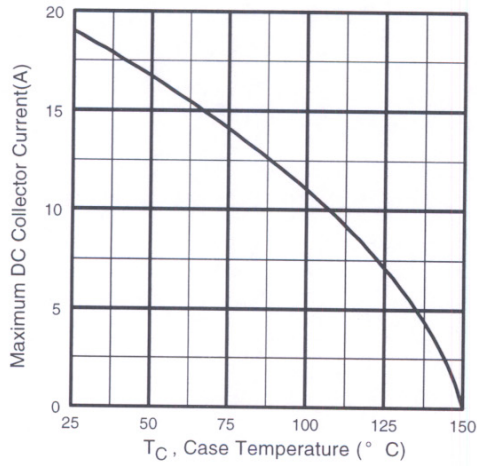


Fig. 4 - Maximum Collector Current vs. Case Temperature

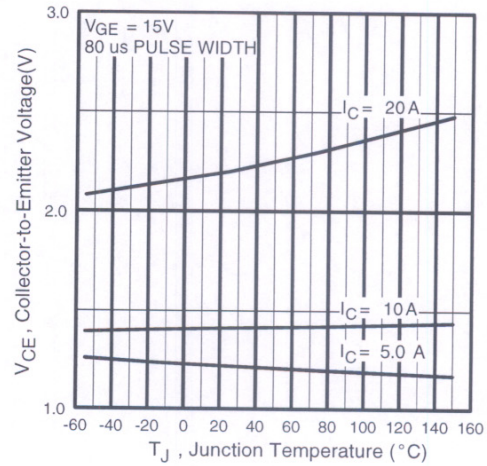


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

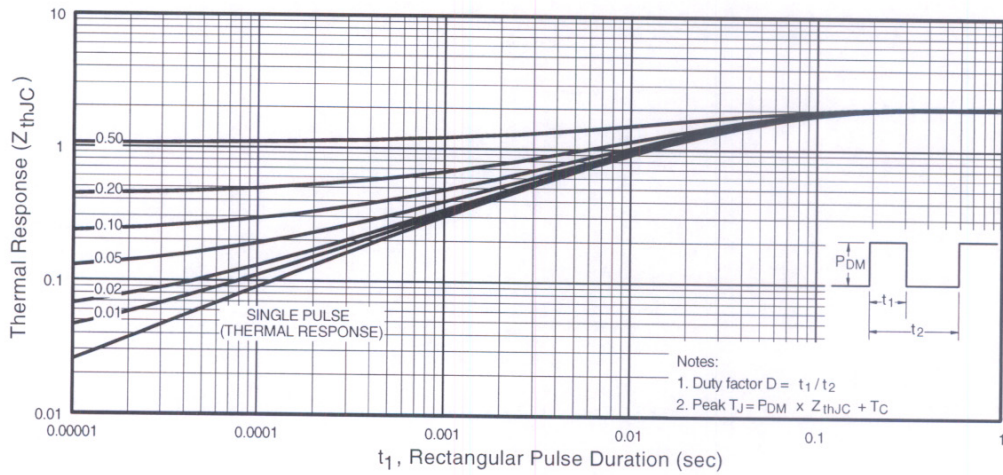


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

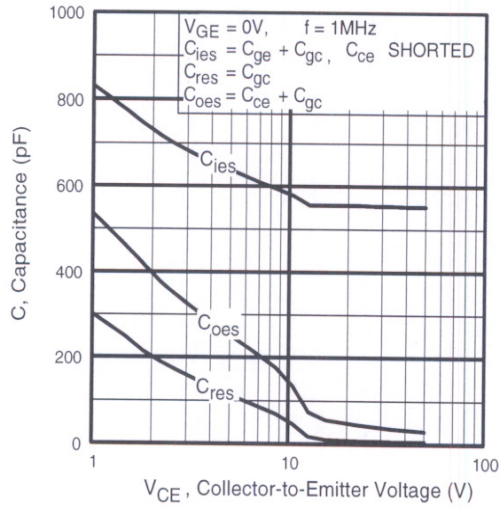


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

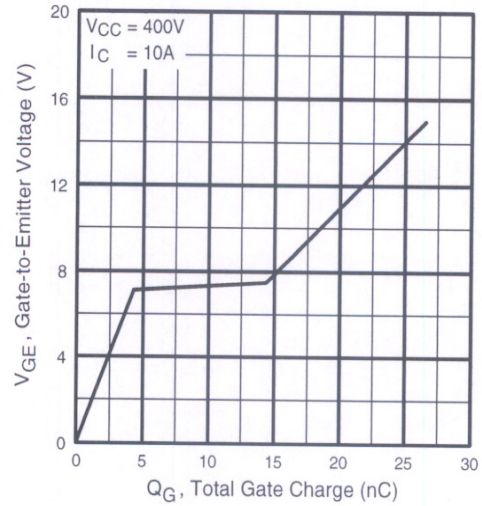


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

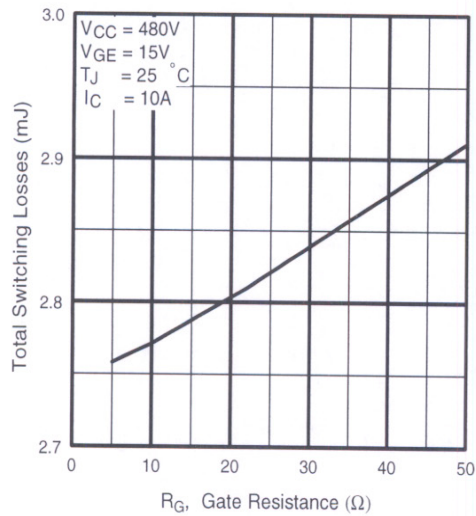


Fig. 9 - Typical Switching Losses vs. Gate Resistance

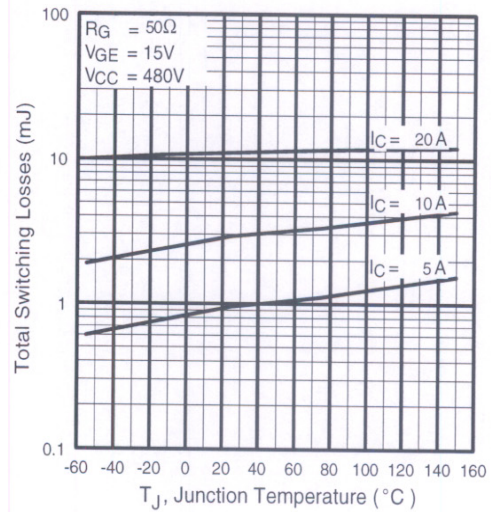


Fig. 10 - Typical Switching Losses vs. Junction Temperature

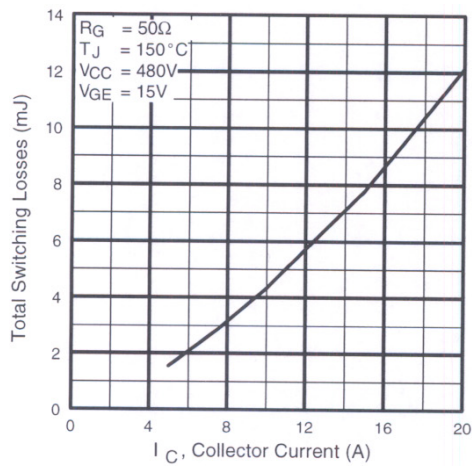


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

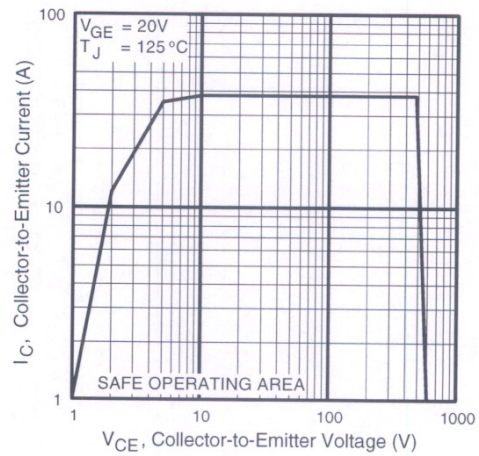


Fig. 12 - Turn-Off SOA

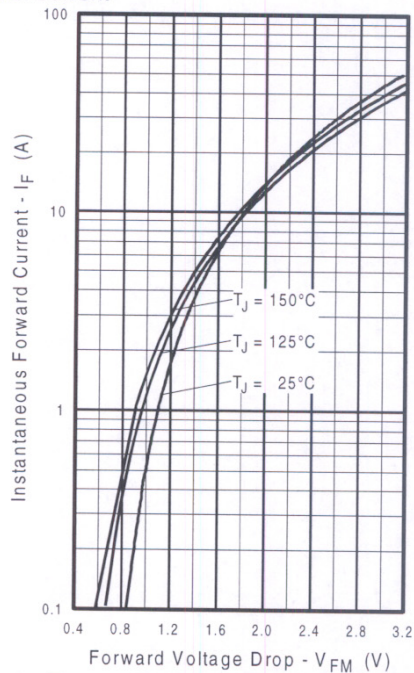


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

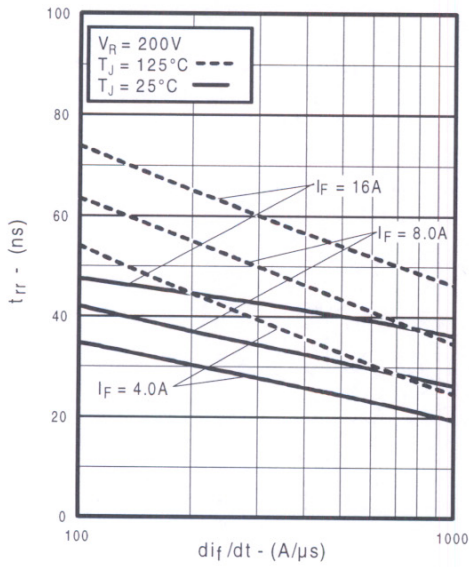


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

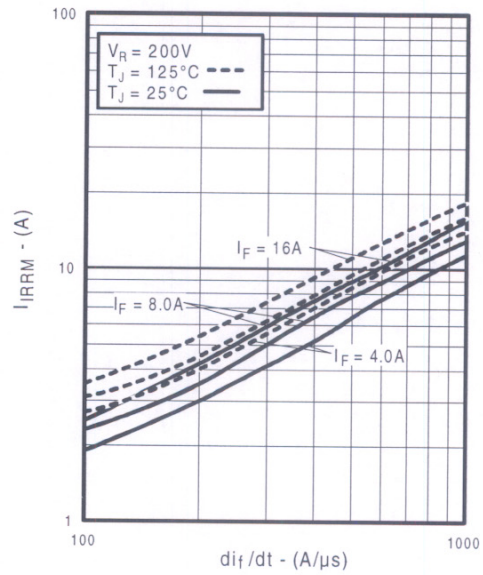


Fig. 15 - Typical Recovery Current vs. di_f/dt

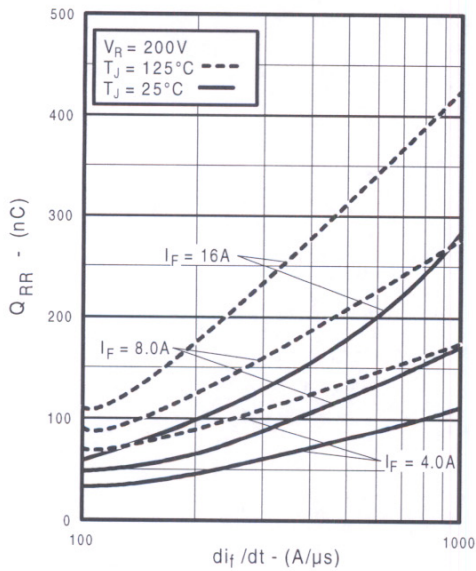


Fig. 16 - Typical Stored Charge vs. di_f/dt

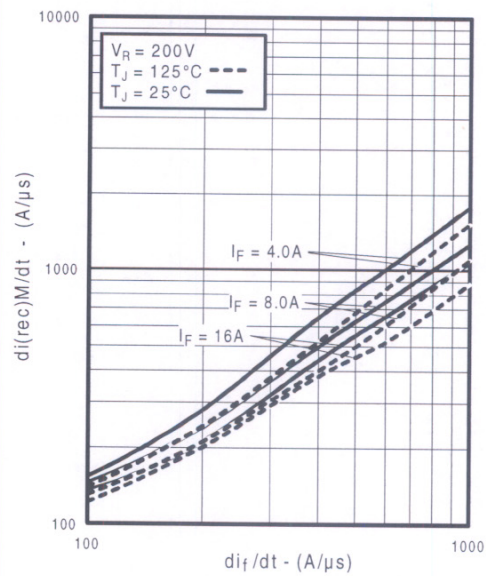


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

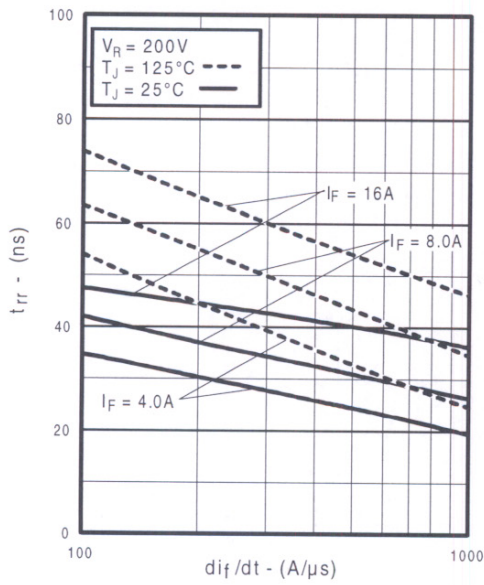


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

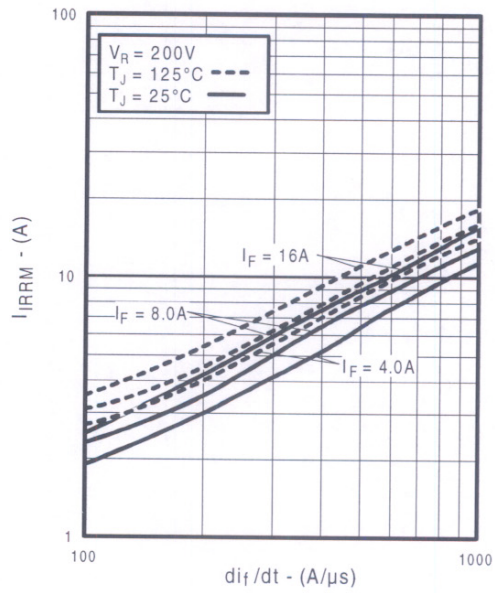


Fig. 15 - Typical Recovery Current vs. di_f/dt

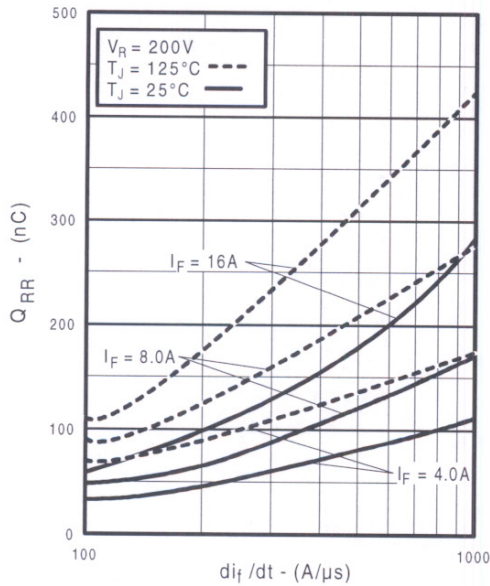


Fig. 16 - Typical Stored Charge vs. di_f/dt

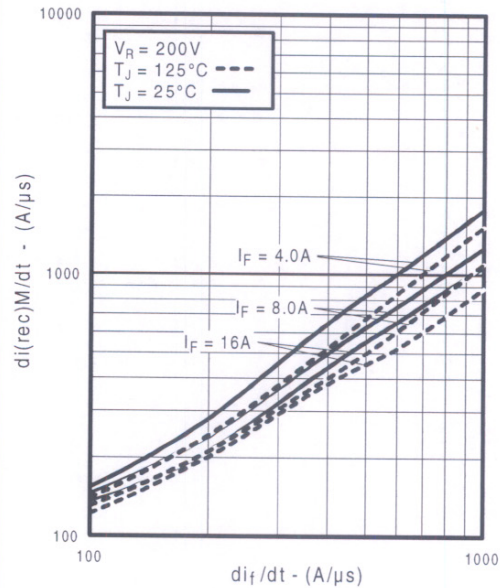


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

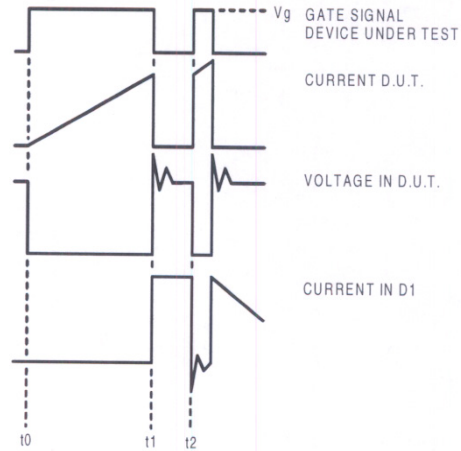


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

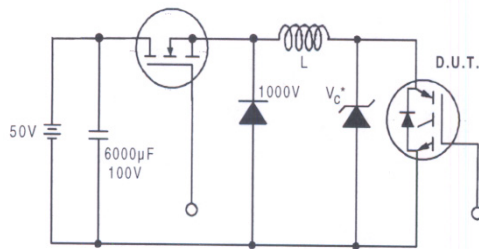


Figure 19. Clamped Inductive Load Test Circuit

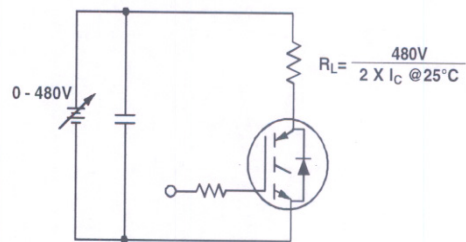


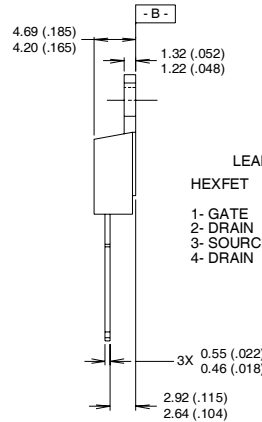
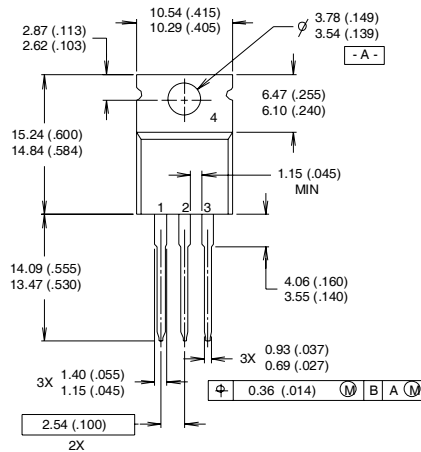
Figure 20. Pulsed Collector Current Test Circuit

IRG4BC20SDPbF

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TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



| LEAD ASSIGNMENTS | |
|------------------|---------------|
| HEXFET | IGBTs, CoPACK |
| 1- GATE | 1- GATE |
| 2- DRAIN | 2- COLLECTOR |
| 3- SOURCE | 3- EMITTER |
| 4- DRAIN | 4- COLLECTOR |

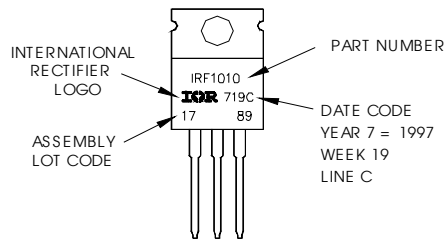
NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH

- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"
Note: "P" in assembly line
position indicates "Lead-Free"



Notes:

- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G = 50\Omega$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width $5.0\mu s$, single shot.

Data and specifications subject to change without notice.

International
IR Rectifier

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